

## PNP HIGH POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/461

### Devices

2N6211

2N6212

2N6213

### Qualified Level

JAN  
JANTX  
JANTXV

### MAXIMUM RATINGS

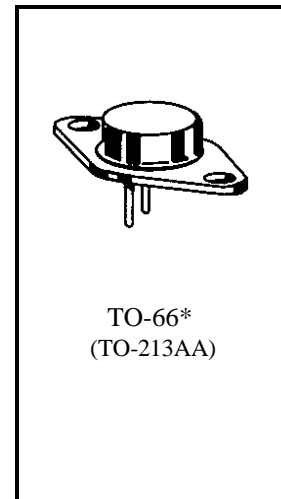
Ratings	Symbol	2N6211	2N6212	2N6213	Unit
Collector-Emitter Voltage	$V_{CEO}$	225	300	350	Vdc
Collector-Base Voltage	$V_{CBO}$	275	350	400	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0			Vdc
Base Current	$I_B$	1.0			Adc
Collector Current	$I_C$	2.0			Adc
Total Power Dissipation	$P_T$	@ $T_A = +25^{\circ}C$ (1)	3.0		W
		@ $T_C = +25^{\circ}C$ (2)	35		W
Operating & Storage Temperature	$T_{op}, T_{stg}$	-55 to +200			$^{\circ}C$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	5.0	$^{\circ}C/W$

1) Derate linearly 17.1 mW/ $^{\circ}C$  for  $T_A > +25^{\circ}C$

2) Derate linearly 200 mW/ $^{\circ}C$  for  $T_C > +25^{\circ}C$



\*See appendix A for package outline

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc, $f = 30$ -60 Hz	2N6211 2N6212 2N6213	$V_{(BR)CEO}$	225 300 350	Vdc
Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc, $f = 30$ -60 Hz, $R_{BE} = 50 \Omega$	2N6211 2N6212 2N6213	$V_{(BR)CER}$	250 325 375	Vdc
Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc, $f = 30$ -60 Hz, $R_{BE} = 50 \Omega$ , $V_{BE} = -1.5$ Vdc	2N6211 2N6212 2N6213	$V_{(BR)CEX}$	275 350 400	Vdc

